# U. Wisconsin CS/ECE 752 Advanced Computer Architecture I 

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Unit 1: Technology, Cost, Performance, Power, etc.
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## This Unit

- What is a computer and what is computer architecture
- Forces that shape computer architecture
- Applications (covered last time)
- Semiconductor technology
- Evaluation metrics: parameters and technology basis
- Cost
- Performance
- Power
- Reliability


## What is Computer Architecture? (review)

- Design of interfaces and implementations...
- Under constantly changing set of external forces...
- Applications: change from above (discussed last time)
- Technology: changes transistor characteristics from below
- Inertia: resists changing all levels of system at once
- To satisfy different constraints
- This course mostly about performance
- Cost
- Power
- Reliability
- Iterative process driven by empirical evaluation
- The art/science of tradeoffs


## Abstraction and Layering

- Abstraction: only way of dealing with complex systems
- Divide world into objects, each with an...
- Interface: knobs, behaviors, knobs $\rightarrow$ behaviors
- Implementation: "black box" (ignorance+apathy)
- Specialists deal with implementation; others interface
- Example: car drivers vs. mechanics
- Layering: abstraction discipline makes life even simpler
- Removes need to even know interfaces of most objects
- Divide objects in system into layers
- Layer X objects
- Implemented in terms of interfaces of layer X-1 objects
- Don't even need to know interfaces of layer X-2 objects


## Abstraction, Layering, and Computers

- Computers are complex systems, built in layers
- Applications
- O/S, compiler
- Firmware, device drivers
- Processor, memory, raw I/O devices
- Digital circuits, digital/analog converters
- Gates
- Transistors
- 99\% of users don't know hardware layers implementation
- 90\% of users don' t know implementation of any layer
- That' s OK, world still works just fine
- But unfortunately, the layers sometimes breakdown
- Someone needs to understand what's "under the hood"


## Gray box: Peeking though the layers

- Layers of abstraction in a car
- Interface (drivers): steering wheel, clutch, shift, brake
- Implementation (mechanic): engine, fuel injection, transmission
- But high-performance drivers know the torque curve
- Achieve maximum performance
- Similar examples for computers
- Cache organization/locality
- Pipeline scheduling/interlocks
- Power users peek across layers



## A Computer Architecture Picture



- Computer architecture
- Definition of ISA to facilitate implementation of software layers
- This course mostly on computer micro-architecture
- Design CPU, Memory, I/O to implement ISA ...


## Semiconductor Technology Background



- Transistor (1947)
- A key invention of 20th century
- Fabrication



## Shaping Force: Technology

- Basic technology element: MOSFET
- MOS: metal-oxide-semiconductor
- Conductor, insulator, semi-conductor
- FET: field-effect transistor

- Solid-state component acts like electrical switch
- Channel conducts source $\rightarrow$ drain when voltage applied to gate
- Channel length: characteristic parameter (short $\rightarrow$ fast)
- Aka "feature size" or "technology"
- Currently: 22nm (0.022 micron)
- Continued miniaturization (scaling) known as "Moore's Law"
- Won' t last forever, physical limits approaching (or are they?)


## Complementary MOS (CMOS)

- Voltages as values
- $\operatorname{Power}\left(\mathrm{V}_{\mathrm{DD}}\right)=1$, Ground $=0$
- Two kinds of MOSFETs
- N-transistors
- Conduct when gate voltage is 1
- Good at passing 0s
- P-transistors
- Conduct when gate voltage is 0
- Good at passing 1s

- CMOS: complementary n-/p- networks form boolean logic


## CMOS Examples

- Example I: inverter
- Case I: input = 0
- P-transistor closed, n-transistor open 0
- Power charges output (1)
- Case II: input = 1
- P-transistor open, n-transistor closed
- Output discharges to ground (0)
- Example II: look at truth table
- $0,0 \rightarrow 1$
$0,1 \rightarrow 1$
- $1,0 \rightarrow 1 \quad 1,1 \rightarrow 0$
- Result: this is a NAND (NOT AND)
- NAND is universal (can build any logic function)



## More About CMOS and Technology

- Two different CMOS families
- SRAM (logic): used to make processors
- Storage implemented as inverter pairs
- Optimized for speed
- DRAM (memory): used to make memory
- Storage implemented as capacitors
- Optimized for density, cost, power
- FLASH memory
- also a technology, but we will discuss later.
- Disk is also a "technology", but isn' t transistor-based


## Aside: VLSI + Manufacturing

- VLSI (very large scale integration)
- Transistor manufacturing process
- Integrated Circuit (1958) as important as transistor itself
- Multi-step photochemical and electrochemical process
- Fixed cost per step
- Cost per transistor shrinks with transistor size
- Other production costs
- Packaging
- Test
- Mask set
- Design

First integrated circuit (1958) Jack Kilby (UW, MSEE, 1950) and Robert Noyce


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## MOSFET Side View



- MOS: three materials needed to make a transistor
- Metal - Aluminum, Tungsten, Copper: conductor
- Oxide - Silicon Dioxide $\left(\mathrm{SiO}_{2}\right)$ : insulator
- Semiconductor - doped Si: conducts under certain conditions
- FET: field effect (the mechanism) transistor
- Voltage on gate: current flows source to drain (transistor on)
- No voltage on gate: no current (transistor off)

Note: former UW Chancellor Wiley co-invented the barrier layer process that enables the use of copper interconnects.

## Manufacturing Process



- Start with silicon wafer
- Grow SiO2
- Deposit photo-resist
- Burn positive bias mask
- Ultraviolet light lithography

- Dissolve unburned photo-resist
- Chemical etch

- Dissolve exposed SiO 2
- Dissolve remaining photo-resist
- Chemical etch
- Continue with device formation


## Manufacturing: Gate formation



- Deposit/grow gate oxide
- Deposit polysilicon
- Deposit/burn/dissolve photo resist
- Etch polysilicon, dissolve unexposed resist
- Bomb wafer with negative ions ( $P$ )
- Doping gates, sources, and drains
- Self-aligning gate process



## Manufacturing Process



- Grow $\mathrm{SiO}_{2}$
- Grow photo-resist
- Burn "via-level-1" mask
- Dissolve unburned photo-resist
- And underlying $\mathrm{SiO}_{2}$
- Grow tungsten "vias"
- Dissolve remaining photo-resist
- Continue with next layer



## Manufacturing Process



- Grow $\mathrm{SiO}_{2}$
- Grow photo-resist
- Burn "wire-level-1" mask
- Dissolve unburned photo-resist
- And underlying $\mathrm{SiO}_{2}$
- Grow copper "wires"
- Dissolve remaining photo-resist
- Continue with next wire layer...
- Typical number of wire layers: 3-8



## Defects

Defective:


Defective:


Slow:


- Defects can arise
- Under-/over-doping
- Over-/under-dissolved insulator
- Mask mis-alignment
- Particle contaminants
- Try to minimize defects
- Process margins
- Design rules
- Minimal transistor size, separation
- Or, tolerate defects
- Redundant or "spare" memory cells


## Empirical Evaluation

- Metrics
- Cost
- Performance
- Power
- Reliability
- Often more important in combination than individually
- Performance/cost (MIPS/\$)
- Performance/power (MIPS/W)
- Basis for
- Design decisions
- Purchasing decisions


## Cost

- Metric: \$
- In grand scheme: CPU accounts for fraction of cost
- Some of that is profit (Intel's, Dell's)

|  | Desktop | Laptop | PDA | Phone |
| :--- | :---: | :---: | :---: | :---: |
| $\$$ | $\$ 100-\$ 300$ | $\$ 150-\$ 350$ | $\$ 50-\$ 100$ | $\$ 10-\$ 20$ |
| $\%$ of total | $10-30 \%$ | $10-20 \%$ | $20-30 \%$ | $20-30 \%$ |
| Other costs | Memory, display, power supply/battery, disk, packaging |  |  |  |

- We are concerned about Intel' s cost (transfers to you)
- Unit cost: costs to manufacture individual chips
- Startup cost: cost to design chip, build the fab line, marketing


## Unit Cost: Integrated Circuit (IC)

- Chips built in multi-step chemical processes on wafers
- Cost / wafer is constant, f(wafer size, number of steps)
- Chip (die) cost is proportional to area
- Larger chips means fewer of them
- Larger chips means fewer working ones
- Why? Uniform defect density
- Chip cost ~ chip area ${ }^{\alpha}$

- $\alpha=2-3$
- Wafer yield: \% wafers that are worth testing
- Die yield: \% chips/wafer that work
- Yield is increasingly non-binary - fast vs slow chips


## Yield/Cost Examples

- Parameters
- wafer yield $=90 \%, \alpha=2$, defect density $=2 / \mathrm{cm}^{2}$

|  |  |  |  |  |  |  |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| Die size $\left(\mathrm{mm}^{2}\right)$ | 100 | 144 | 196 | 256 | 324 | 400 |
| Die yield | $23 \%$ | $19 \%$ | $16 \%$ | $12 \%$ | $11 \%$ | $10 \%$ |
| 6 " Wafer | $139(31)$ | $90(16)$ | $62(9)$ | $44(5)$ | $32(3)$ | $23(2)$ |
| 8 8" Wafer | $256(59)$ | $177(32)$ | $124(19)$ | $90(11)$ | $68(7)$ | $52(5)$ |
| $10 "$ Wafer | $431(96)$ | $290(53)$ | $206(32)$ | $153(20)$ | $116(13)$ | $90(9)$ |


|  | Wafer <br> cost | Defect <br> $\left(/ \mathrm{cm}^{2}\right)$ | Area <br> $\left(\mathrm{mm}^{2}\right)$ | Dies | Yield | Die <br> Cost | Package <br> Cost (pins) $)$ | Test <br> cost | Total |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| Intel 486DX2 | $\$ 1200$ | 1.0 | 81 | 181 | $54 \%$ | $\$ 12$ | $\$ 11(168)$ | $\$ 12$ | $\$ 35$ |
| IBM PPC601 | $\$ 1700$ | 1.3 | 196 | 66 | $27 \%$ | $\$ 95$ | $\$ 3(304)$ | $\$ 21$ | $\$ 119$ |
| DEC Alpha | $\$ 1500$ | 1.2 | 234 | 53 | $19 \%$ | $\$ 149$ | $\$ 30(431)$ | $\$ 23$ | $\$ 202$ |
| Intel Pentium | $\$ 1500$ | 1.5 | 296 | 40 | $9 \%$ | $\$ 417$ | $\$ 19(273)$ | $\$ 37$ | $\$ 473$ |

## Startup Costs (NREs)

- Startup costs: must be amortized over chips sold
- Research and development: ~\$300M per chip
- 1500 person-years @ \$200K per
- Fabrication facilities: $\sim \$ 2 B$ per new line
- Clean rooms (bunny suits), lithography, testing equipment
- If you sell 10 M chips, fab startup adds $\sim \$ 200 /$ chip
- Must amortize the fab costs over many designs!
- R\&D costs add \$30/chip for 10 M chips
- Reuse basic design many times
- Pentium Pro, Pentium II, Pentium III, and Pentium M share common microarchitecture (more or less)


## Moore' s Effect on Cost

- Scaling has opposite effects on unit and startup costs
+ Reduces unit integrated circuit cost
- Either lower cost for same functionality...
- Or same cost for more functionality
- Increases startup cost
- More expensive fabrication equipment
- Takes longer to design, verify, and test chips


## Performance

- Two definitions
- Latency (execution time): time to finish a fixed task
- Throughput (bandwidth): number of tasks in fixed time
- Very different: throughput can exploit parallelism, latency cannot
- Baking bread analogy
- Often contradictory
- Choose definition that matches goals (most frequently thruput)
- Example: move people from $A$ to $B, 10$ miles
- Car: capacity $=5$, speed $=60$ miles $/$ hour
- Bus: capacity $=60$, speed $=20$ miles $/$ hour
- Latency: car = $\mathbf{1 0} \mathbf{~ m i n}$, bus $=30 \mathrm{~min}$
- Throughput: car = 15 PPH (count return trip), bus = 60 PPH


## Performance Improvement

- Processor $A$ is $X$ times faster than processor $B$ if
- Latency $(P, A)=$ Latency $(P, B) / X$
- Throughput $(P, A)=\operatorname{Throughput}(P, B) * X$
- Processor $A$ is $X \%$ faster than processor $B$ if
- Latency(P,A) = Latency(P,B) / (1+X/100)
- $\operatorname{Throughput(P,A)=\operatorname {Throughput(P,B)}*(1+X/100)~}$
- Car/bus example
- Latency? Car is 3 times (and 200\%) faster than bus
- Throughput? Bus is 4 times (and $300 \%$ ) faster than car


## What Is 'P' in Latency(P,A)?

- Program
- Latency(A) makes no sense, processor executes some program
- But which one?
- Actual target workload?
+ Accurate
- Not portable/repeatable, overly specific, hard to pinpoint problems
- Some representative benchmark program(s)?
+ Portable/repeatable, pretty accurate
- Hard to pinpoint problems, may not be exactly what you run
- Some small kernel benchmarks (micro-benchmarks)
+ Portable/repeatable, easy to run, easy to pinpoint problems
- Not representative of complex behaviors of real programs


## SPEC Benchmarks

- SPEC (Standard Performance Evaluation Corporation)
- http://www.spec.org/
- Consortium of companies that collects, standardizes, and distributes benchmark programs
- Post SPECmark results for different processors
- 1 number that represents performance for entire suite
- Benchmark suites for CPU, Java, I/O, Web, Mail, etc.
- Updated every few years: so companies don' t target benchmarks
- SPEC CPU 2006
- 12 "integer": bzip, gccs, perl, mcf, etc.
- 17 "floating point": mesa (openGL), equake, facerec, etc.
- Written in C and Fortran (a few in C++)


## Other Benchmarks

- Parallel benchmarks
- SPLASH2 - Stanford Parallel Applications for Shared Memory
- NAS
- SPEC' s OpenMP benchmarks
- SPECjbb - Java multithreaded database-like workload
- Transaction Processing Council (TPC)
- TPC-C: On-line transaction processing (OLTP)
- TPC-H/R: Decision support systems (DSS)
- TPC-W: E-commerce database backend workload
- Have parallelism (intra-query and inter-query)
- Heavy I/O and memory components


## Adding/Averaging Performance Numbers

- You can add latencies, but not throughput
- Latency $(P 1+P 2, A)=$ Latency $(P 1, A)+$ Latency $(P 2, A)$
- Throughput(P1+P2,A) != Throughput(P1,A) + Throughput(P2,A)
- 1 mile @ 30 miles/hour + 1 mile @ 90 miles/hour
- Average is not 60 miles/hour
- 0.033 hours at 30 miles/hour +0.01 hours at 90 miles/hour
- Average is only 47 miles/hour! ( 2 miles / ( $0.033+0.01$ hours))
- $\operatorname{Throughput}(\mathrm{P} 1+\mathrm{P} 2, \mathrm{~A})=$
$1 /[(1 /$ Throughput(P1,A)) + (1/ Throughput(P2,A))]
- Same goes for means (averages)
- Arithmetic: $(1 / \mathrm{N}) * \sum_{P=1 . . \mathrm{N}}$ Latency $(P)$
- For units that are proportional to time (e.g., latency)
- Harmonic: $\mathrm{N} / \sum_{P=1 . \mathrm{N}} 1 /$ Throughput( P$)$
- For units that are inversely proportional to time (e.g., throughput)
- Geometric: ${ }^{N} \sqrt{ } \Pi_{P=1 . . \mathrm{N}}$ Speedup(P)
- For unitless quantities (e.g., speedups)


## SPECmark

- Reference machine: Sun Ultra Enterprise II
- Latency SPECmark
- For each benchmark
- Take odd number of samples: on both machines
- Choose median
- Take latency ratio (Sun Ultrasparc / your machine)
- Take GMEAN of ratios over all benchmarks
- Throughput SPECmark
- Run multiple benchmarks in parallel on multiple-processor system
- Recent (latency) leaders
- SPECint: Intel 3.2 GHz Xeon X5482 (24.6)
- SPECfp: Fujitsu SPARC Enterprise M8000 (25)


## CPU Performance Equation

- Multiple aspects to performance: helps to isolate them
- Latency $(\mathrm{P}, \mathrm{A})=$ seconds $/$ program =
- (instructions / program) * (cycles / instruction) * (seconds / cycle)
- Instructions / program: dynamic instruction count
- Function of program, compiler, instruction set architecture (ISA)
- Cycles / instruction: CPI
- Function of program, compiler, ISA, micro-architecture
- Seconds / cycle: clock period
- Function of micro-architecture, technology parameters
- For low latency (better performance) minimize all three
- Hard: often pull against the other


## Danger: Partial Performance Metrics

- Micro-architects often ignore dynamic instruction count
- Typically work in one ISA/one compiler $\rightarrow$ treat it as fixed
- Not always accurate for multithreaded workloads!
- CPU performance equation becomes
- seconds / instruction = (cycles / instruction) * (seconds / cycle)
- This is a latency measure, if we care about throughput ...
- Instructions / second = (instructions / cycle) * (cycles / second)
- MIPS (millions of instructions per second)
- Instructions / second * $10^{-6}$
- Cycles / second: clock frequency (in MHz)
- Example: $\mathrm{CPI}=2$, clock $=500 \mathrm{MHz}$, what is MIPS?
- 0.5 * $500 \mathrm{MHz} * 10^{-6}=250 \mathrm{MIPS}$
- Example problem situation:
- compiler removes instructions, program faster
- However, "MIPS" goes down (misleading)


## MIPS and MFLOPS (MegaFLOPS)

- Problem: MIPS may vary inversely with performance
- Some optimizations actually add instructions
- Work per instruction varies (e.g., FP mult vs. integer add)
- ISAs are not equivalent
- MFLOPS: like MIPS, but counts only FP ops, because...
+ FP ops can' t be optimized away
+ FP ops have longest latencies anyway
+ FP ops are same across machines
- May have been valid in 1980, but today...
- Many programs are "integer", i.e., light on FP
- Loads from memory take much longer than FP divide
- Even FP instructions sets are not equivalent
- Upshot: Neither MIPS nor MFLOPS are broadly useful


## Danger: Partial Performance Metrics II

- Micro-architects often ignore dynamic instruction count...
- ... but general public (mostly) also ignores CPI
- Equates clock frequency with performance!!
- Which processor would you buy?
- Processor A: CPI $=2$, clock $=500 \mathrm{MHz}$
- Processor B: CPI = 1, clock $=300 \mathrm{MHz}$
- Probably $A$, but $B$ is faster (assuming same ISA/compiler)
- (Not so) Recent example
- 800 MHz PentiumIII faster than 1 GHz Pentium4
- Same ISA and compiler


## Cycles per Instruction (CPI)

- This course is mostly about improving CPI
- Cycle/instruction for average instruction
- IPC = 1/CPI
- Used more frequently than CPI, but harder to compute with
- Different instructions have different cycle costs
- E.g., integer add typically takes 1 cycle, FP divide takes > 10
- Assumes you know something about instruction frequencies
- CPI example
- A program executes equal integer, FP, and memory operations
- Cycles per instruction type: integer $=1$, memory $=2, \mathrm{FP}=3$
- What is the CPI? $(0.33 * 1)+(0.33 * 2)+(0.33 * 3)=2$
- Caveat: this sort of calculation ignores dependences completely
- Back-of-the-envelope arguments only


## Another CPI Example

- Assume a processor with instruction frequencies and costs
- Integer ALU: 50\%, 1 cycle
- Load: 20\%, 5 cycle
- Store: $10 \%, 1$ cycle
- Branch: 20\%, 2 cycle
- Which change would improve performance more?
- A. Branch prediction to reduce branch cost to 1 cycle?
- B. A bigger data cache to reduce load cost to 3 cycles?
- Compute CPI
- Base $=0.5^{*} 1+0.2 * 5+0.1^{*} 1+0.2 * 2=2$
- $\mathrm{A}=0.5 * 1+0.2 * 5+0.1^{*} 1+0.2^{*} 1=1.8$
- $B=0.5^{*} 1+0.2^{*} 3+0.1^{*} 1+0.2^{*} 2=1.6$ (winner)


## Increasing Clock Frequency: Pipelining



- CPU is a pipeline: compute stages separated by latches
- Clock period: maximum delay of any stage
- Number of gate levels in stage
- Delay of individual gates (these days, wire delay more important)


## Increasing Clock Frequency: Pipelining

- Reduce pipeline stage delay
- Reduce logic levels and wire lengths (better design)
- Complementary to technology efforts (described later)
- Increase number of pipeline stages (multi-stage operations)
- Often causes CPI to increase
- At some point, actually causes performance to decrease
- "Optimal" pipeline depth is program and technology specific
- Remember example
- PentiumIII: 12 stage pipeline, 800 MHz
faster than
- Pentium4: 22 stage pipeline, 1 GHz
- Current Intel design (Haswell): more like PentiumIII


## CPI and Clock Frequency

- System components "clocked" independently
- $\mathrm{CPI}=\mathrm{CPI}_{\mathrm{CPU}}+\mathrm{CPI}_{\text {MEM }}$
- E.g., Increasing processor clock frequency doesn't improve memory performance
- Example
- Processor A: $\mathrm{CPI}_{\text {CPU }}=1, \mathrm{CPI}_{\text {MEM }}=1$, clock $=500 \mathrm{MHz}$
- Base: $\mathrm{CPI}=2 \rightarrow \mathrm{IPC}=0.5 \rightarrow$ MIPS $=250$
- What is the speedup if we double clock frequency?
- Clock *= $2 \rightarrow \mathrm{CPI}_{\text {MEM }} *=2 \rightarrow \mathrm{CPI}_{\text {MEM }}=2$
- New: CPI $=3 \rightarrow$ IPC $=0.33 \rightarrow$ MIPS $=333$
- Speedup $=333 / 250=1.33 \ll 2$

$$
\begin{aligned}
& \text { Speedup } \\
& =\text { Told/Tnew }
\end{aligned}
$$

- What about an infinite clock frequency?
- Only a x2 speedup (Example of Amdahl' s Law)


## Measuring CPI

- How are CPI and execution-time actually measured?
- Execution time: time (Unix): wall clock + CPU + system
- CPI = CPU time / (clock frequency * dynamic insn count)
- How is dynamic instruction count measured?
- Want CPI breakdowns $\left(\mathrm{CPI}_{\mathrm{CPU}}, \mathrm{CPI}_{\text {MEM }}\right.$, etc.) to see what to fix
- CPI breakdowns
- Hardware event counters
- Calculate CPI using counter frequencies/event costs
- Cycle-level micro-architecture simulation (e.g., SimpleScalar)
+ Measures breakdown "exactly" provided
+ Models micro-architecture faithfully
+ Ran realistic workload
- Method of choice for many micro-architects (and you)


## Improving CPI

- This course is more about improving CPI than frequency
- Historically, clock accounts for 70\%+ of performance improvement
- Achieved via deeper pipelines
- That will (have to) change
- Deep pipelining is not power efficient
- Physical speed limits are approaching
- 1GHz: 1999, 2GHz: 2001, 3GHz: 2002, 3.8GHz: 2004, 5GHz: 2008
- Intel Core 2: 1.8-3.2GHz: 2008
- Techniques we will look at
- Caching, speculation, multiple issue, out-of-order issue
- Vectors, multiprocessing, more...
- Moore helps because CPI reduction requires transistors
- The definition of parallelism is "more transistors"
- But best example is caches


## Moore' s Effect on Performance

- Moore's Curve: common interpretation of Moore' s Law
- "CPU performance doubles every 18 months"
- Self fulfilling prophecy
- 2 X every 18 months is $\sim 1 \%$ per week
- Q: Would you add a feature that improved performance $20 \%$ if it took 8 months to design and test?
- Processors under Moore' s Curve (arrive too late) fail spectacularly



## Performance Rules of Thumb

- Make common case fast
- "Amdahl's Law"
- Speedup $_{\text {overall }}=1 /\left(\left(1-\right.\right.$ fraction $\left._{x}\right)+$ fraction $_{x} /$ Speedup $\left._{x}\right)$
- Corollary: don't optimize $5 \%$ to the detriment of other $95 \%$
- Speedup $_{\text {overall }}=1 /((1-5 \%)+5 \% /$ infinity $)=1.05$
- Build a balanced system
- Don't over-engineer capabilities that cannot be utilized
- Try to be "bound" by the most expensive resourses (if not everywhere)
- Design for actual, not peak, performance
- For actual performance $X$, machine capability must be $>X$


## Little’ s Law

- Key Relationship between latency and bandwidth:
- Average number in system = arrival rate * avg. holding time
- Example:
- How big a wine cellar should I build?
- My family drinks (and buys) an average of 4 bottles per week
- On average, I want to age my wine 5 years
- bottles in cellar = 4 bottles/week * 52 weeks/year * 5 years
- = 1040 bottles (!!!)


## More Little' s Law

- How many outstanding cache misses?
- Want to sustain $5 \mathrm{~GB} / \mathrm{s}$ bandwidth
- 64 byte blocks
- 100 ns miss latency
- Requests in system = arrival rate * time in system
$=(5 \mathrm{~GB} / \mathrm{s} / 64$ byte blocks $) * 100 \mathrm{~ns}$
$=8$ misses
- That's an AVERAGE. Need to support many more if we hope to sustain this bandwidth. (Rule of thumb is 2 X )


## Transistor Speed, Power, and Reliability

- Transistor characteristics and scaling impact:
- Switching speed
- Power
- Reliability
- "Undergrad" gate delay model for architecture
- Each Not, NAND, NOR, AND, OR gate has delay of " 1 "
- Reality is not so simple


## Transistors and Wires



IBM SOI Technology

## Transistors and Wires



IBM CMOS7, 6 layers of copper wiring From sides © Krste Asanovic, mit CS/ECE 752 (Wood): Technology, Cost, Performance, Power, etc.

## Simple RC Delay Model

- Switching time is a RC circuit (charge or discharge)
- R - Resistance: slows rate of current flow
-W - Depends on material, length, cross-section area
- C - Capacitance: electrical charge storage
$H-$ Depends on material, area, distance
- Voltage affects speed, too



## Resistance

- Transistor channel resistance
- function of $\mathrm{V}_{\mathrm{g}}$ (gate voltage)
- Wire resistance (negligible for short wires)



## Capacitance

- Source/Drain capacitance
- Gate capacitance

- Wire capacitance (negligible for short wires)



## RC Delay

- Delay = RC



## Which is faster? Why?



## Transistor Width

- "Wider" transistors have lower resistance, more drive
- Specified per-device

- Useful for driving large "loads" like long or off-chip wires


## RC Delay Model Ramifications

- Want to reduce resistance
- "wide" drive transistors (width specified per device)
- Short wires
- Want to reduce capacitance
- Number of connected devices
- Less-wide transistors (gate capacitance of next stage)
- Short wires



## Transistor Scaling



- Transistor length is key property of a "process generation"
- 90 nm refers to the transistor gate length, same for all transistors
- Shrink transistor length:
- Lower resistance of channel (shorter)
- Lower gate/source/drain capacitance
- Result: transistor drive strength linear as gate length shrinks

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## Wires



- Resistance fixed by (length*resistivity) / (height*width)
- Intel' s 45nm process uses copper with $3.3 \Omega / \mu \mathrm{m}$ on M1-M3
- Capacitance depends on geometry of surrounding wires and relative permittivity, $\varepsilon_{r}$, of dielectric
- silicon dioxide $\varepsilon_{r}=3.9$, new low-k dielectrics in range 1.2-3.1
- Intel' s 45 nm M1-M3 have $0.20 \mathrm{fF} / \mu \mathrm{m}$ ( 160 nm pitch)


## Wire Delay

- RC Delay of wires
- Resistance proportional to length
- Capacitance proportional to length
- Result: delay of a wire is quadratic in length
- Insert "inverter" repeaters for long wires to
- Bring it back to linear delay



## Moore's Effect on RC Delay

- Scaling helps reduce wire and gate delays
+ Wires become shorter (Length $\downarrow \rightarrow$ Resistance $\downarrow$ )
+ Wire "surface areas" become smaller (Capacitance $\downarrow$ )
+ Transistors become shorter (Resistance $\downarrow$ )
+ Transistors become narrower (Capacitance $\downarrow$, Resistance $\uparrow$ )
- But also increases wire and gate delays
- Wires become narrower (Resistance $\uparrow$ )
- Wires become closer together (Resistance $\uparrow$ )
- Gate insulator thickness becomes smaller (Capacitance $\uparrow$ )
- Distance between wires becomes smaller (Capacitance $\uparrow$ )
- Bottom line: Long wires dominate delay


## Improving RC Delay

- Exploit good effects of scaling
- Fabrication technology improvements
+ Use copper instead of aluminum for wires ( $\rho \downarrow \rightarrow$ Resistance $\downarrow$ )
+ Use lower-dielectric insulators ( $\kappa \downarrow \rightarrow$ Capacitance $\downarrow$ )
+ Design implications
+ Use bigger cross-section wires (Area $\uparrow \rightarrow$ Resistance $\downarrow$ )
- Typically means taller, otherwise fewer of them
- Need more layers $\rightarrow$ higher fabrication cost
- Increases "surface area" and capacitance (Capacitance $\uparrow$ )
+ Use wider transistors (Area $\uparrow \rightarrow$ Resistance $\downarrow$ )
- Increases capacitance (not for you, for upstream transistors)
- Increases power (to charge/discharge capacitance)
- Use selectively


## Another Constraint: Power and Energy

- Power (Watt or Joule/Second): short-term (peak, max)
- Was mostly a dissipation (heat) concern, now \$\$\$ too
- Power-density (Watt/cm²): important related metric
- Thermal cycle: power dissipation $\uparrow \rightarrow$ power density $\uparrow \rightarrow$ temperature $\uparrow \rightarrow$ resistance $\uparrow \rightarrow$ power dissipation $\uparrow \ldots$
- Cost (and form factor): packaging, heat sink, fan, etc.
- Energy (Joule): long-term
- Mostly a consumption concern
- Primary issue is battery life (cost, weight of battery, too)
- Low-power implies low-energy, but not the other way around
- 10 years ago, nobody cared except in embedded apps


## Power Density

## Power Density (W/mm2)



## Sources of Energy Consumption



Dynamic power:

- Capacitor Charging (85-90\% of active power)
- Energy is $1 / 2 \mathrm{CV}^{2}$ per transition
- Short-Circuit Current ( $10-15 \%$ of active power)
- When both p and n transistors turn on during signal transition

Static power:

- Subthreshold Leakage (dominates when inactive)
- Transistors don' t turn off completely
- Diode Leakage (negligible)
- Parasitic source and drain diodes leak to substrate


## Moore' s Effect on Power

- Scaling has largely good effects on local power
+ Shorter wires/smaller transistors (Length $\downarrow \rightarrow$ Capacitance $\downarrow$ )
- Shorter transistor length (Resistance $\downarrow$, Capacitance $\downarrow$ )
- Global effects largely undone by increased transistor counts
- Scaling has a largely negative effect on power density
+ Transistor/wire power decreases linearly
- Transistor/wire density decreases quadratically
- Power-density increases linearly
- Thermal cycle
- Controlled somewhat by reduced $\mathrm{V}_{\mathrm{DD}}(5 \rightarrow 3.3 \rightarrow 1.6 \rightarrow 1.3 \rightarrow 1.1)$
- Reduced $V_{D D}$ sacrifices some switching speed


## Reducing Power

- Power proportional to $\mathrm{CV}_{\mathrm{DD}}{ }^{2 \mathrm{f}}$
- Reduce supply voltage ( $\mathrm{V}_{\mathrm{DD}}$ )
+ Reduces dynamic power quadratically and static power linearly
- But poses a tough choice regarding $\mathrm{V}_{\mathrm{T}}$
- Constant $\mathrm{V}_{\mathrm{T}}$ slows circuit speed $\rightarrow$ clock frequency $\rightarrow$ performance
- Reduced $\mathrm{V}_{\mathrm{T}}$ increases static power exponentially
- Reduce clock frequency (f)
+ Reduces dynamic power linearly
- Doesn' t reduce static power
- Reduces performance linearly
- Generally doesn't make sense without also reduced $\mathrm{V}_{\mathrm{DD}} \ldots$
- Except that frequency can be adjusted cycle-to-cycle and locally
- More on this later


## Dynamic Voltage Scaling (DVS)

- Dynamic voltage scaling (DVS)
- OS reduces voltage/frequency when peak performance not needed

|  | Mobile PentiumIII <br> "SpeedStep" | TM5400 <br> "LongRun" | Intel X-Scale <br> (StrongARM2) |
| :--- | :---: | :---: | :---: |
| Frequency | $300-1000 \mathrm{MHz}$ <br> $(50 \mathrm{MHz}$ steps) | $200-700 \mathrm{MHz}$ <br> $(33 \mathrm{MHz}$ steps) | $50-800 \mathrm{MHz}$ <br> $(50 \mathrm{MHz}$ steps) |
| Voltage | $0.9-1.7 \mathrm{~V}$ <br> $(0.1 \mathrm{~V}$ steps) | $1.1-1.6 \mathrm{~V}$ <br> (continuous) | $0.7-1.65 \mathrm{~V}$ <br> (continuous) |
| High-speed | 3400MIPS @ 34W | 1600MIPS @ 2W | 800MIPS @ 0.9W |
| Low-power | 1100MIPS @ 4.5W | 300MIPS @ 0.25W | 62MIPS @ 0.01W |

$\pm$ X-Scale is power efficient (6200 MIPS/W), but not IA32 compatible

## Reducing Power: Processor Modes

- Modern electrical components have low-power modes
- Note: no low-power disk mode, magnetic (non-volatile)
- "Standby" mode
- Turn off internal clock
- Leave external signal controller and pins on
- Restart clock on interrupt
$\pm$ Cuts dynamic power linearly, doesn' t effect static power
- Laptops go into this mode between keystrokes
- "Sleep" mode
- Flush caches, OS may also flush DRAM to disk
- Turn off processor power plane
- Needs a "hard" restart
+ Cuts dynamic and static power
- Laptops go into this mode after $\sim 10$ idle minutes


## Reliability

- Mean Time Between Failures (MTBF)
- How long before you have to reboot or buy a new one
- CPU reliability small in grand scheme
- Software most unreliable component in a system
- Much more difficult to specify \& test
- Much more of it
- Most unreliable hardware component ... disk
- Subject to mechanical wear


## Moore' s Bad Effect on Reliability

- CMOS devices: CPU and memory
- Historically almost perfectly reliable
- Moore has made them less reliable over time
- Two common sources of electrical faults
- Energetic particle strikes (e.g., from sun)
- Randomly charge nodes, cause bits to flip, transient
- Electro-migration: change in electrical interfaces/properties
- Temperature-driven, happens gradually, permanent
- Large, high-energy transistors are immune to these effects
- Scaling makes node energy closer to particle energy
- Scaling increases power-density which increases temperature
- Memory (DRAM) was hit first: denser, smaller devices than SRAM
- Now SRAM is more susceptible (smaller capacitances)
- Flip-flops (e.g., registers and microarchitectural state) at risk???


## Moore' s Good Effect on Reliability

- The key to providing reliability is redundancy
- The same scaling that makes devices less reliable...
- Also increase device density to enable redundancy
- Classic example
- Error correcting code (ECC) for DRAM
- ECC now on caches and register files for many designs
- More reliability techniques later
- Today’ s big open questions
- How to efficiently protect logic?
- Can architectural techniques help hardware reliability?
- Can architectural techniques help with software reliability?


## Summary: A Global Look at Moore

- Device scaling (Moore's Law)
+ Increases performance
- Reduces transistor/wire delay
- Gives us more transistors with which to reduce CPI
+ Reduces local power consumption
- Which is quickly undone by increased integration
- Aggravates power-density and temperature problems
- Aggravates reliability problem
+ But gives us the transistors to solve it via redundancy
+ Reduces unit cost
- But increases startup cost
- Will we fall off Moore' s Cliff? (for real, this time?)
- What's next: nanotubes, quantum-dots, optical, spin-tronics, DNA?


## Summary

- What is computer architecture
- Abstraction and layering: interface and implementation, ISA
- Shaping forces: application and semiconductor technology
- Moore's Law
- Cost
- Unit and startup
- Performance
- Latency and throughput
- CPU performance equation: insn count * CPI * clock frequency
- Power and energy
- Dynamic and static power
- Reliability


## A Computer Archtecture Picture



- Mostly about micro-architecture
- Mostly about CPU/Memory
- Mostly about general-purpose
- Mostly about performance
- We' Il still only scratch the surface

